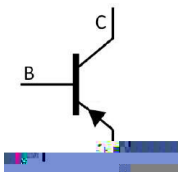
WR0<50P ḾḾÞ SQS ÆḾч s ll ㄱ Silicon PNP transistor in a TO-92LM Plastic Package.

лъ 5VG99:+D,Ӣ´
Complementary pair with 2SD667(A).

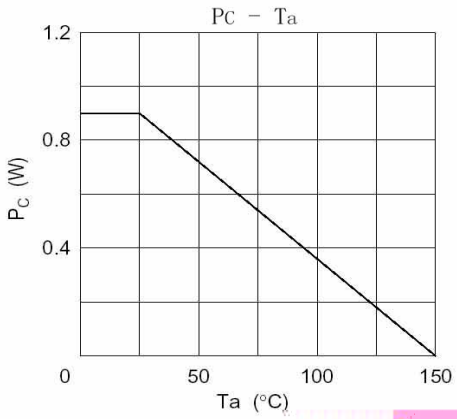
ᵮ Ӈ ļ ı ' ѽ ᶻ
Low frequency power amplifier.

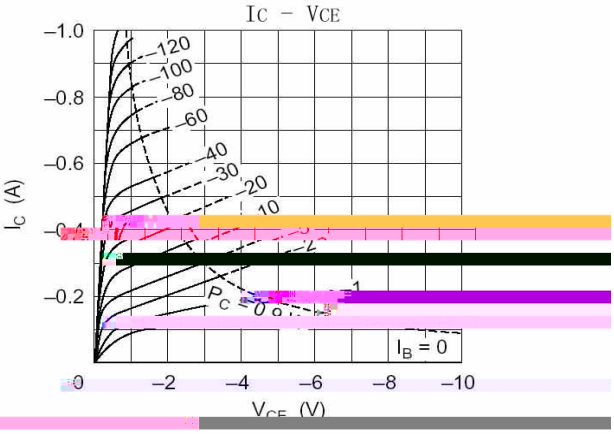


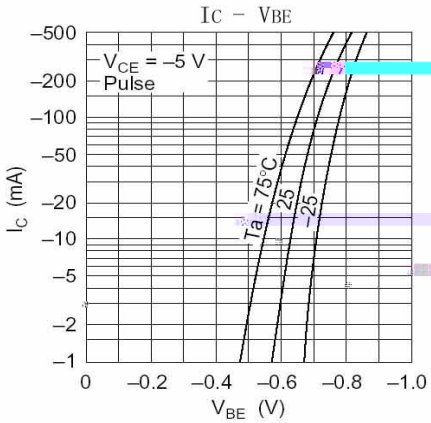


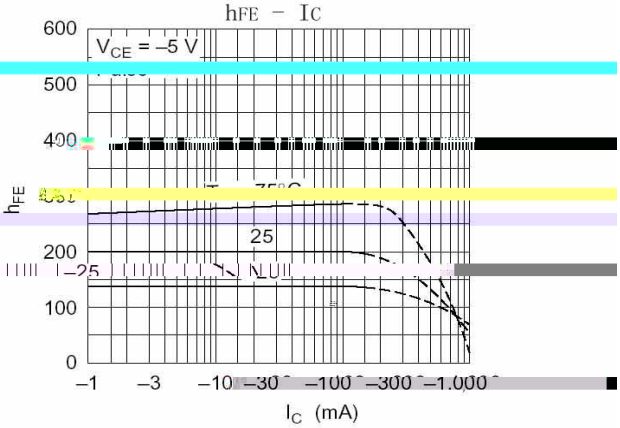

PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

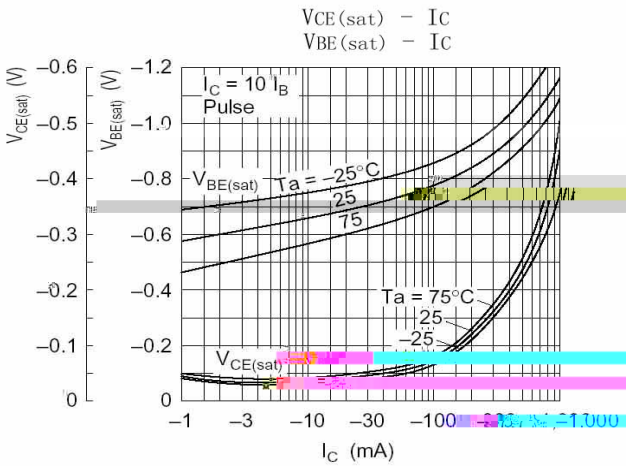
| v Ѽ<br>Parameter | ϒ N<br>Symbol | | Ѽ Ө<br>Rating | D Ң<br>Unit |
|---|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | | -120 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | 2SB647 | -80 | V |
| | | 2SB647A | -100 | |
| Emitter to Base Voltage | $V_{EBO}$ | | -5.0 | V |
| Collector Current (DC) | $I_C$ | | -1.0 | A |
| Collector Current(Pulse) | $I_{CP}$ | | -2.0 | A |
| Collector Power Dissipation | $P_C$ | | 900 | mW |
| Junction Temperature | $T_j$ | | 150 | |
| Storage Temperature Range | T | | | |

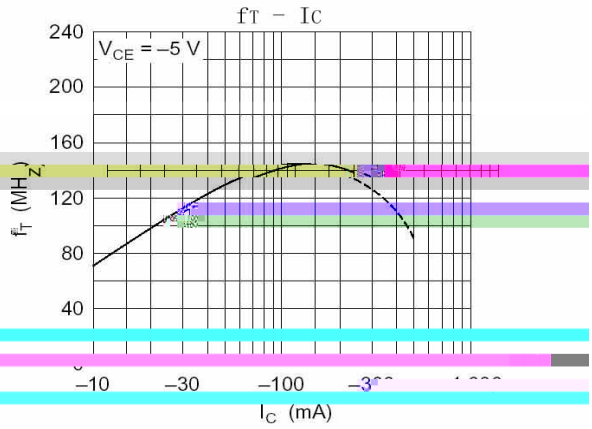

PC – Ta
PC (W)
1.2
0.8
0.4
0
50
100
150
Ta (°C)


IC – VCE
IC (A)
–1.0
–0.8
–0.6
–0.2
120
100
80
60
40
30
20
10
IB = 0
–2
–4
–6
–8
–10


IC – VBE
VCE = –5 V
Pulse
IC (mA)
–500
–200
–100
–50
–20
–10
–5
–2
–1
Ta = 75°C
25
–25
0
–0.2
–0.4
–0.6
–0.8
–1.0
VBE (V)

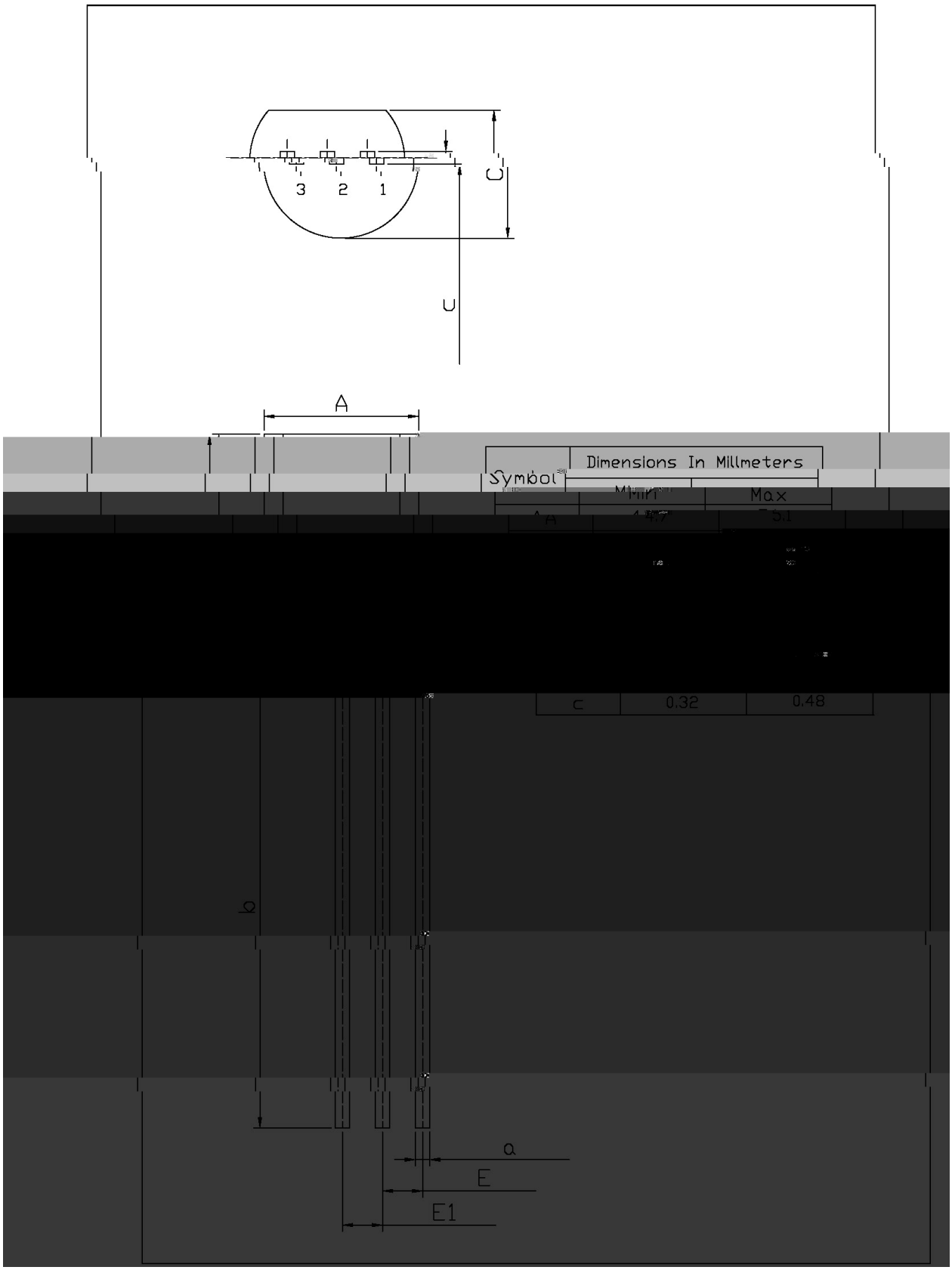

hFE – IC
VCE = –5 V
hFE
600
500
400
200
100
0
25
–25
–1
–3
–10
–30
–100
–300
–1,000
IC (mA)


VCE(sat) – IC
VBE(sat) – IC
IC = 10 IB
Pulse
VCE(sat) (V)
VBE(sat) (V)
–0.6
–0.5
–0.4
–0.3
–0.2
–0.1
0
–1.2
–1.0
–0.8
–0.6
–0.4
–0.2
VBE(sat)
Ta = –25°C
25
75
Ta = 75°C
25
–25
VCE(sat)
–1
–3
–10
–30
–100
–1,000
IC (mA)


fT – IC
VCE = –5 V
fT (MHz)
240
200
160
120
80
40
–10
–30
–100
IC (mA)

# TO-92LM

Unit: mm

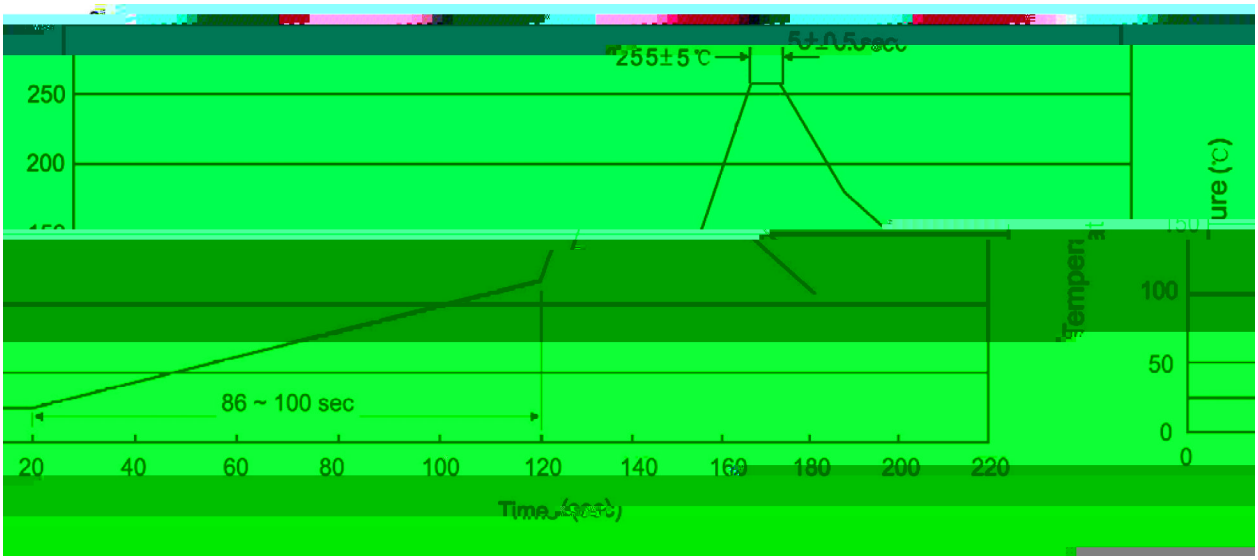





| | |
|---|---|
| ᴗ ˝ χ | |
| EU= | ᵻᵡ ϛ ᴎ Γϧ |
| E97 : D χ | ᵻᵡ ʒ ᴺ Γϧ |
| F= | ᵻᵡ k ᵻᴴ ᶜ ⁶ Γϧ |
| ---- χ | ᵻᵡ ᵻ ᶠ ᵑ̋ ᴺ Γϧ ᵻ ᵩ ᵻ ᶠ ᵑ̋ ᴺ Ψ ᖘ |

Note:

| | |
|---|---|
| BR: | Company Code. |
| B647A: | Product Type. |
| C: | $h_{FE}$ Classifications Symbol |
| ****: | Lot No. Code,code change with Lot No. |




ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ł